



FDD3682

# FDD3682

## N-Channel PowerTrench<sup>®</sup> MOSFET 100V, 32A, 36mΩ

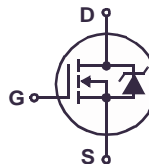
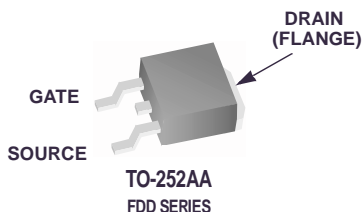
### Features

- $r_{DS(ON)} = 32m\Omega$  (Typ.),  $V_{GS} = 10V$ ,  $I_D = 32A$
- $Q_g(tot) = 18.5nC$  (Typ.),  $V_{GS} = 10V$
- Low Miller Charge
- Low  $Q_{RR}$  Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101

Formerly developmental type 82755

### Applications

- DC/DC converters and Off-Line UPS
- Distributed Power Architectures and VRMs
- Primary Switch for 24V and 48V Systems
- High Voltage Synchronous Rectifier
- Direct Injection / Diesel Injection System
- 42V Automotive Load Control
- Electronic Valve Train System



### MOSFET Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current		
	Continuous ( $T_C = 25^\circ C$ , $V_{GS} = 10V$ )	32	A
	Continuous ( $T_C = 100^\circ C$ , $V_{GS} = 10V$ )	23	A
	Continuous ( $T_{amb} = 25^\circ C$ , $V_{GS} = 10V$ , $R_{\theta JA} = 52^\circ C/W$ )	5.5	A
	Pulsed	Figure 4	A
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	55	mJ
$P_D$	Power dissipation	95	W
	Derate above $25^\circ C$	0.63	W/ $^\circ C$
$T_J, T_{STG}$	Operating and Storage Temperature	-55 to 175	$^\circ C$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction to Case TO-252	1.58	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252	100	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area	52	$^\circ C/W$

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: <http://www.aecouncil.com/>

Reliability data can be found at: <http://www.fairchildsemi.com/products/discrete/reliability/index.html>.

All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

## Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD3682	FDD3682	TO-252AA	330mm	16mm	2500 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$B_{VDSS}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	100	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{V}$ $V_{GS} = 0\text{V}$ $T_C = 150^\circ\text{C}$	-	-	1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

### On Characteristics

$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$	2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 32\text{A}$ , $V_{GS} = 10\text{V}$	-	0.032	0.036	$\Omega$
		$I_D = 16\text{A}$ , $V_{GS} = 6\text{V}$	-	0.040	0.060	
		$I_D = 32\text{A}$ , $V_{GS} = 10\text{V}$ , $T_C = 175^\circ\text{C}$	-	0.080	0.090	

### Dynamic Characteristics

$C_{ISS}$	Input Capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	-	1250	-	pF
$C_{OSS}$	Output Capacitance		-	190	-	pF
$C_{RSS}$	Reverse Transfer Capacitance		-	45	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V}$ to 10V	-	18.5	28	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0\text{V}$ to 2V	-	2.4	3.6	nC
$Q_{gs}$	Gate to Source Gate Charge	$V_{DD} = 50\text{V}$ $I_D = 32\text{A}$ $I_g = 1.0\text{mA}$	-	6.5	-	nC
$Q_{gs2}$	Gate Charge Threshold to Plateau		-	4.1	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	4.6	-	nC

### Resistive Switching Characteristics ( $V_{GS} = 10\text{V}$ )

$t_{ON}$	Turn-On Time	$V_{DD} = 50\text{V}$ , $I_D = 32\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GS} = 16\Omega$	-	-	83	ns
$t_{d(ON)}$	Turn-On Delay Time		-	9	-	ns
$t_r$	Rise Time		-	46	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	24	-	ns
$t_f$	Fall Time		-	26	-	ns
$t_{OFF}$	Turn-Off Time		-	-	75	ns

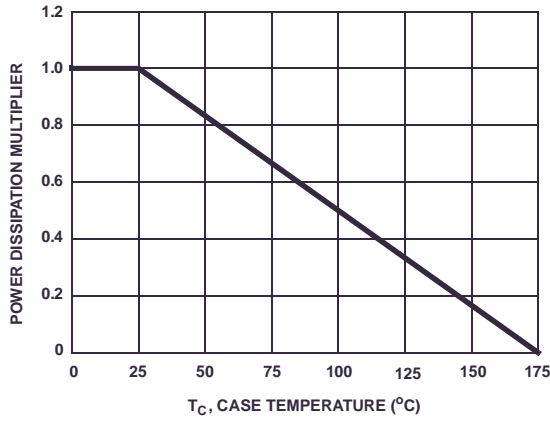
### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Voltage	$I_{SD} = 32\text{A}$	-	-	1.25	V
		$I_{SD} = 16\text{A}$	-	-	1.0	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 32\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	55	ns
$Q_{RR}$	Reverse Recovery Charge	$I_{SD} = 32\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	92	nC

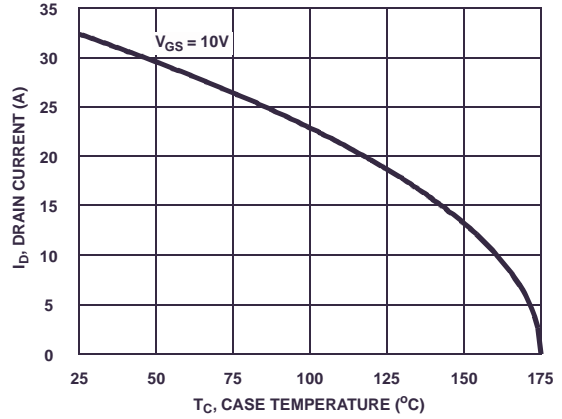
#### Notes:

1: Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.27\text{mH}$ ,  $I_{AS} = 20\text{A}$ .

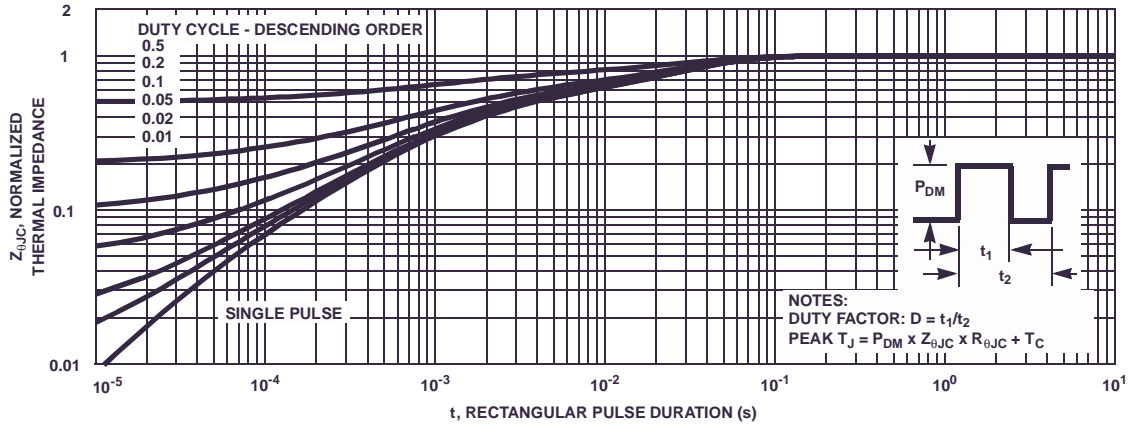
**Typical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted



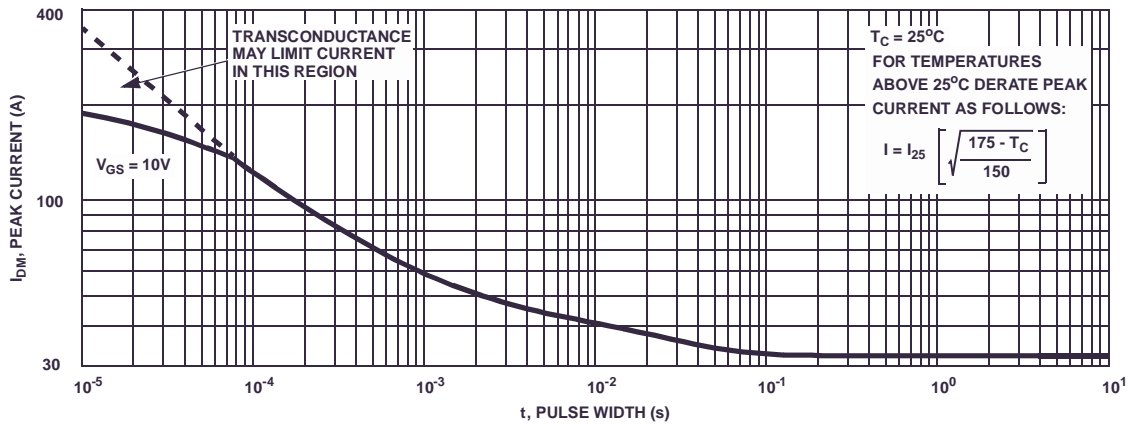
**Figure 1. Normalized Power Dissipation vs Ambient Temperature**



**Figure 2. Maximum Continuous Drain Current vs Case Temperature**

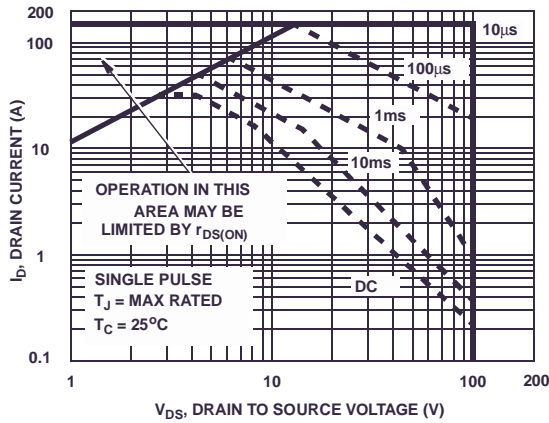


**Figure 3. Normalized Maximum Transient Thermal Impedance**

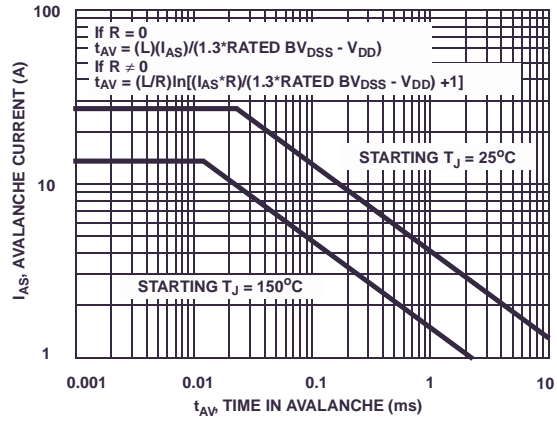


**Figure 4. Peak Current Capability**

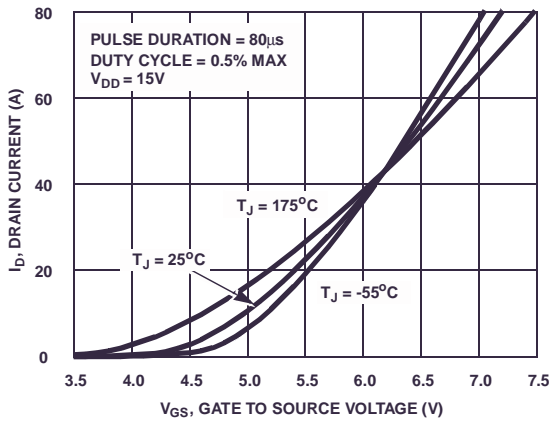
**Typical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted



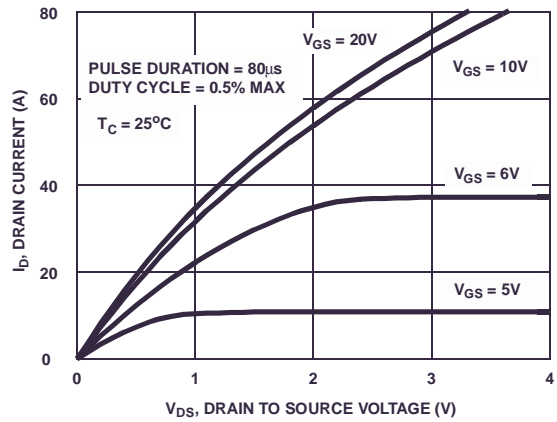
**Figure 5. Forward Bias Safe Operating Area**



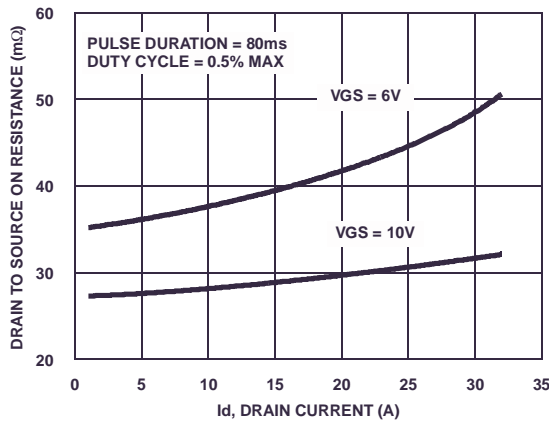
NOTE: Refer to Fairchild Application Notes AN7514 and AN7515  
**Figure 6. Unclamped Inductive Switching Capability**



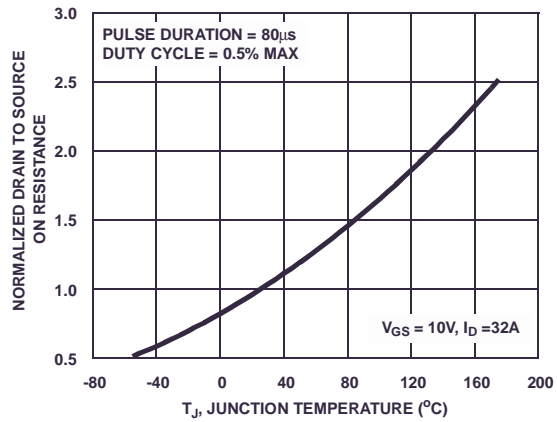
**Figure 7. Transfer Characteristics**



**Figure 8. Saturation Characteristics**

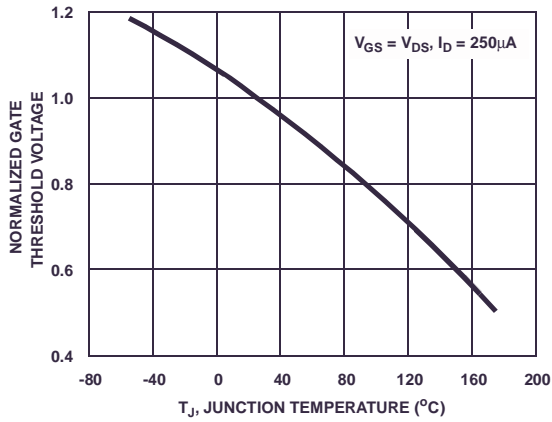


**Figure 9. Drain to Source On Resistance vs Drain Current**

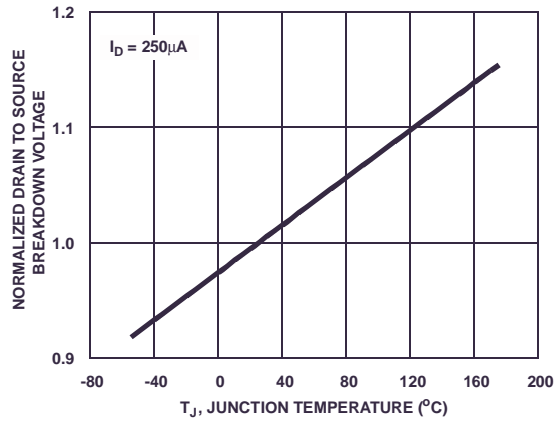


**Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature**

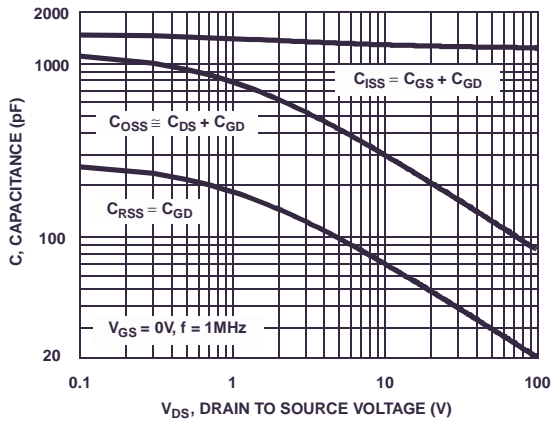
**Typical Characteristics**  $T_C = 25^\circ\text{C}$  unless otherwise noted



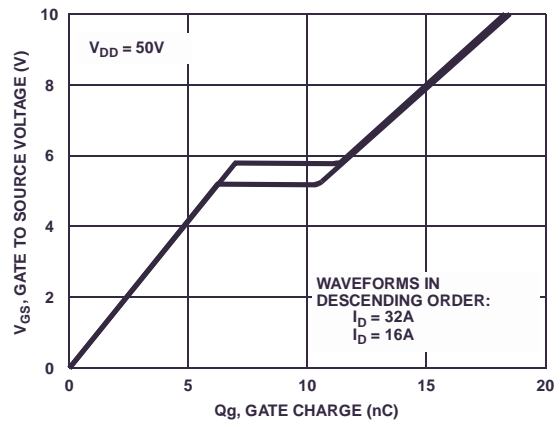
**Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature**



**Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature**



**Figure 13. Capacitance vs Drain to Source Voltage**



**Figure 14. Gate Charge Waveforms for Constant Gate Currents**

Test Circuits and Waveforms

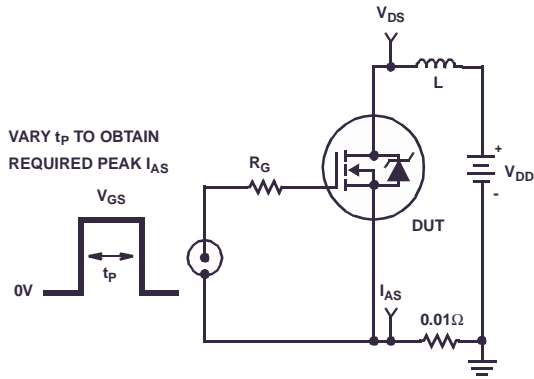


Figure 15. Unclamped Energy Test Circuit



Figure 16. Unclamped Energy Waveforms

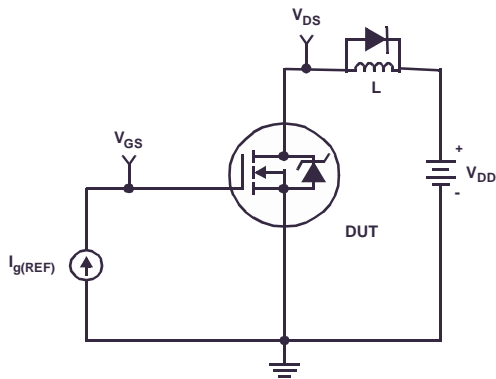


Figure 17. Gate Charge Test Circuit

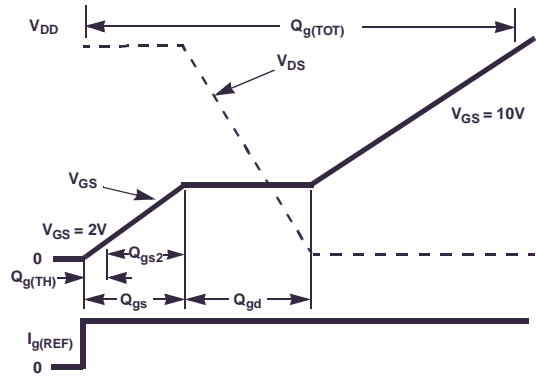


Figure 18. Gate Charge Waveforms

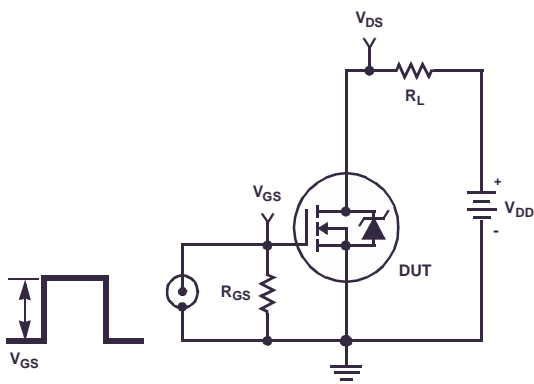


Figure 19. Switching Time Test Circuit

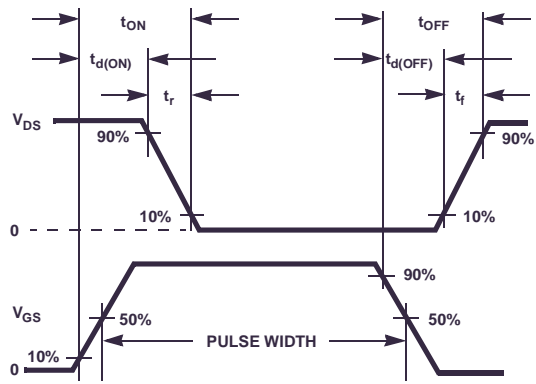


Figure 20. Switching Time Waveforms

## Thermal Resistance vs. Mounting Pad Area

The maximum rated junction temperature,  $T_{JM}$ , and the thermal resistance of the heat dissipating path determines the maximum allowable device power dissipation,  $P_{DM}$ , in an application. Therefore the application's ambient temperature,  $T_A$  ( $^{\circ}C$ ), and thermal resistance  $R_{\theta JA}$  ( $^{\circ}C/W$ ) must be reviewed to ensure that  $T_{JM}$  is never exceeded. Equation 1 mathematically represents the relationship and serves as the basis for establishing the rating of the part.

$$P_{DM} = \frac{(T_{JM} - T_A)}{R_{\theta JA}} \quad (\text{EQ. 1})$$

In using surface mount devices such as the TO-252 package, the environment in which it is applied will have a significant influence on the part's current and maximum power dissipation ratings. Precise determination of  $P_{DM}$  is complex and influenced by many factors:

1. Mounting pad area onto which the device is attached and whether there is copper on one side or both sides of the board.
2. The number of copper layers and the thickness of the board.
3. The use of external heat sinks.
4. The use of thermal vias.
5. Air flow and board orientation.
6. For non steady state applications, the pulse width, the duty cycle and the transient thermal response of the part, the board and the environment they are in.

Fairchild provides thermal information to assist the designer's preliminary application evaluation. Figure 21 defines the  $R_{\theta JA}$  for the device as a function of the top copper (component side) area. This is for a horizontally positioned FR-4 board with 1oz copper after 1000 seconds of steady state power with no air flow. This graph provides the necessary information for calculation of the steady state junction temperature or power dissipation. Pulse applications can be evaluated using the Fairchild device Spice thermal model or manually utilizing the normalized maximum transient thermal impedance curve.

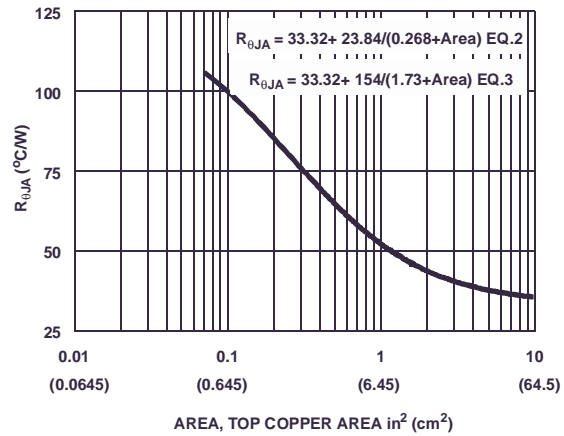
Thermal resistances corresponding to other copper areas can be obtained from Figure 21 or by calculation using Equation 2 or 3. Equation 2 is used for copper area defined in inches square and equation 3 is for area in centimeter square. The area, in square inches or square centimeters is the top copper area including the gate and source pads.

$$R_{\theta JA} = 33.32 + \frac{23.84}{(0.268 + Area)} \quad (\text{EQ. 2})$$

Area in Inches Squared

$$R_{\theta JA} = 33.32 + \frac{154}{(1.73 + Area)} \quad (\text{EQ. 3})$$

Area in Centimeters Squared



**Figure 21. Thermal Resistance vs Mounting Pad Area**

### PSPICE Electrical Model

.SUBCKT FDD3682 2 1 3 ; rev Jun 2002

Ca 12 8 4e-10  
Cb 15 14 6e-10  
Cin 6 8 1.22e-9

Dbody 7 5 DbodyMOD  
Dbreak 5 11 DbreakMOD  
Dplcap 10 5 DplcapMOD

Ebreak 11 7 17 18 112  
Eds 14 8 5 8 1  
Egs 13 8 6 8 1  
Esg 6 10 6 8 1  
Evtbres 6 21 19 8 1  
Evttemp 20 6 18 22 1

It 8 17 1

Lgate 1 9 4.88e-9  
Ldrain 2 5 1.0e-9  
Lsource 3 7 2.24e-9

RLgate 1 9 48.8  
RLdrain 2 5 10  
RLsource 3 7 22.4

Mmed 16 6 8 8 MmedMOD  
Mstro 16 6 8 8 MstroMOD  
Mweak 16 21 8 8 MweakMOD

Rbreak 17 18 RbreakMOD 1  
Rdrain 50 16 RdrainMOD 10.5e-3  
Rgate 9 20 1.8  
RSLC1 5 51 RSLCMOD 1.0e-6  
RSLC2 5 50 1.0e3  
Rsource 8 7 RsourceMOD 11.9e-3  
Rvthres 22 8 RvthresMOD 1  
Rvtemp 18 19 RvtempMOD 1  
S1a 6 12 13 8 S1AMOD  
S1b 13 12 13 8 S1BMOD  
S2a 6 15 14 13 S2AMOD  
S2b 13 15 14 13 S2BMOD

Vbat 22 19 DC 1

ESLC 51 50 VALUE={{(V(5,51)/ABS(V(5,51)))\*(PWR(V(5,51)/(1e-6\*70),2.5))}}

.MODEL DbodyMOD D (IS=2.4E-12 RS=4.4e-3 TRS1=2.0e-3 TRS2=4.5e-7  
+ CJO=9e-10 M=0.58 TT=2.9e-8 XTI=4.0)

.MODEL DbreakMOD D (RS=0.6 TRS1=1.4e-3 TRS2=-5.0e-5)

.MODEL DplcapMOD D (CJO=2.75e-10 IS=1.0e-30 N=10 M=0.56)

.MODEL MstroMOD NMOS (VTO=4.16 KP=32 IS=1e-30 N=10 TOX=1 L=1u W=1u)

.MODEL MmedMOD NMOS (VTO=3.48 KP=2.7 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=1.8)

.MODEL MweakMOD NMOS (VTO=2.96 KP=0.068 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=18 RS=0.1)

.MODEL RbreakMOD RES (TC1=1.1e-3 TC2=-1.1e-8)

.MODEL RdrainMOD RES (TC1=1.5e-2 TC2=4e-5)

.MODEL RSLCMOD RES (TC1=3.0e-3 TC2=2.9e-6)

.MODEL RsourceMOD RES (TC1=1e-3 TC2=1e-6)

.MODEL RvthresMOD RES (TC1=-3.9e-3 TC2=-1.4e-5)

.MODEL RvtempMOD RES (TC1=-3.5e-3 TC2=1.3e-6)

.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-5.0 VOFF=-2.0)

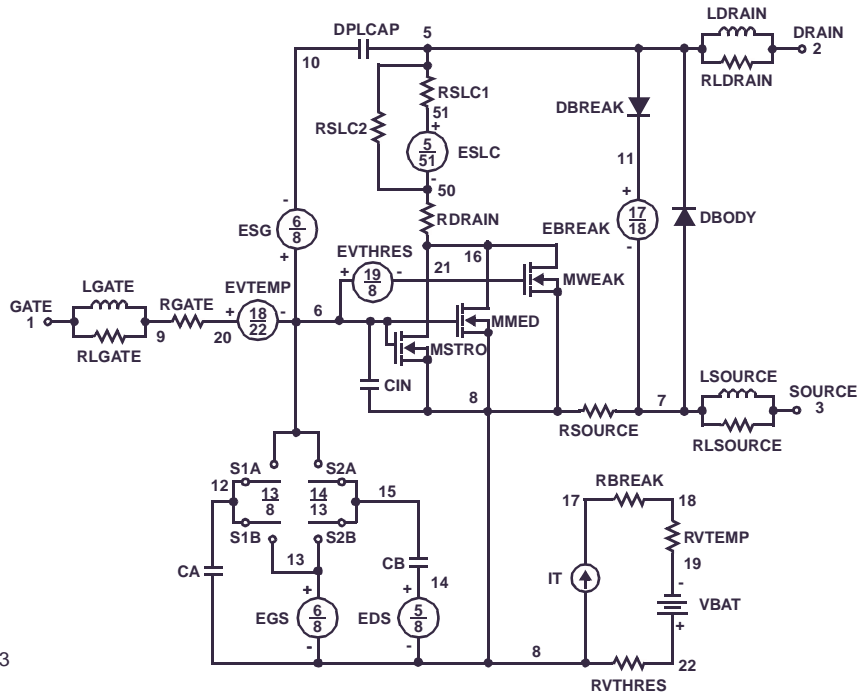
.MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-2.0 VOFF=-5.0)

.MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-0.4 VOFF=0.3)

.MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.3 VOFF=-0.4)

.ENDS

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.







### SPICE Thermal Model

REV 20 Jun 2002

FDD3682\_JC TH TL

```

CTHERM1 TH 6 1.6e-3
CTHERM2 6 5 4.5e-3
CTHERM3 5 4 5.0e-3
CTHERM4 4 3 8.0e-3
CTHERM5 3 2 8.2e-3
CTHERM6 2 TL 4.7e-2
    
```

```

R THERM1 TH 6 3.3e-2
R THERM2 6 5 7.9e-2
R THERM3 5 4 9.5e-2
R THERM4 4 3 1.4e-1
R THERM5 3 2 2.9e-1
R THERM6 2 TL 6.7e-1
    
```

### SABER Thermal Model

SABER thermal model FDD3682

template thermal\_model th tl

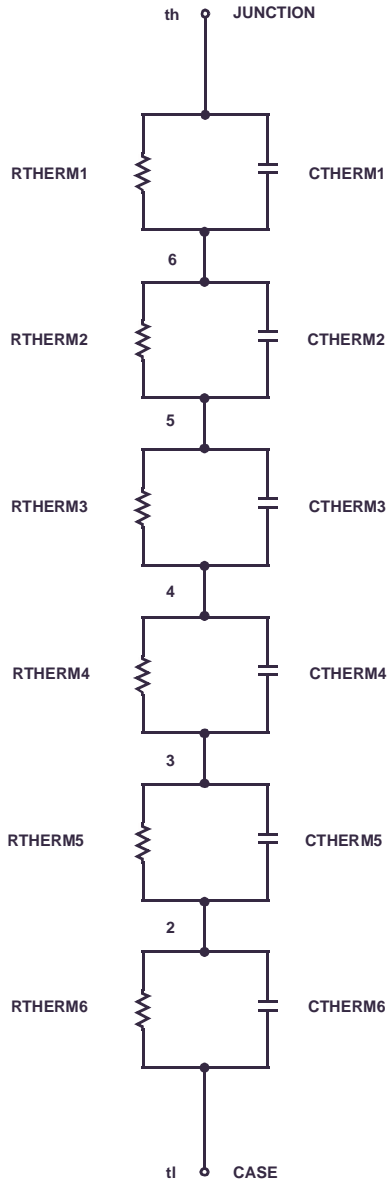
thermal\_c th, tl

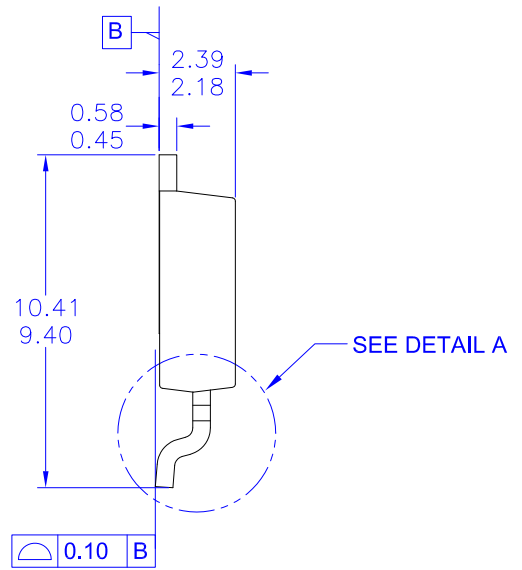
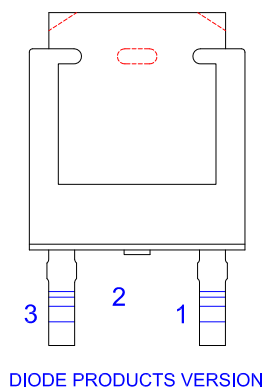
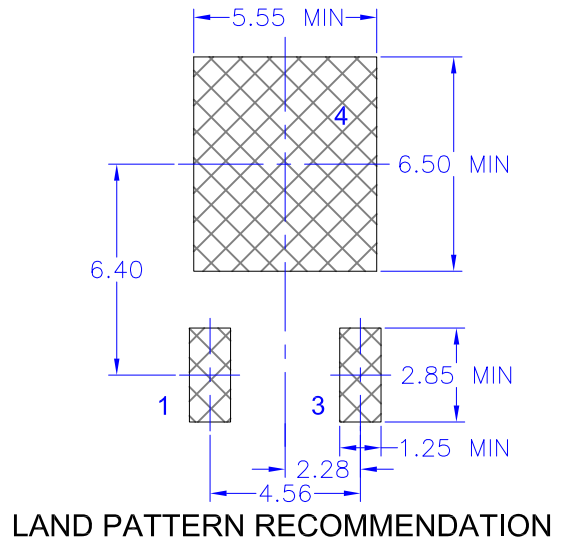
```

{
ctherm.ctherm1 th 6 =1.6e-3
ctherm.ctherm2 6 5 =4.5e-3
ctherm.ctherm3 5 4 =5.0e-3
ctherm.ctherm4 4 3 =8.0e-3
ctherm.ctherm5 3 2 =8.2e-3
ctherm.ctherm6 2 tl =4.7e-2
    
```

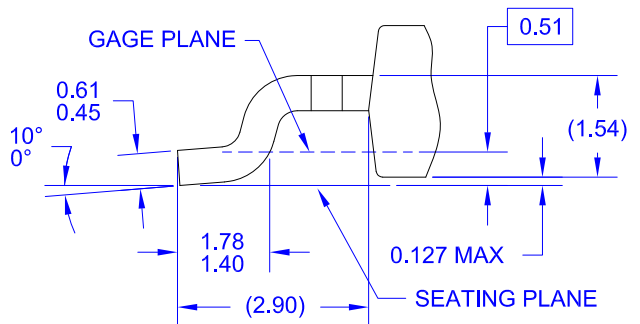
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rtherm.rtherm1 th 6 =3.3e-2
rtherm.rtherm2 6 5 =7.9e-2
rtherm.rtherm3 5 4 =9.5e-2
rtherm.rtherm4 4 3 =1.4e-1
rtherm.rtherm5 3 2 =2.9e-1
rtherm.rtherm6 2 tl =6.7e-1
}
    
```





- NOTES: UNLESS OTHERWISE SPECIFIED
- A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE C, VARIATION AA.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
  - D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
  - E) TRIMMED CENTER LEAD IS PRESENT ONLY FOR DIODE PRODUCTS
  - F) DIMENSIONS ARE EXCLUSIVE OF BURSS, MOLD FLASH AND TIE BAR EXTRUSIONS.
  - G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
  - H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV10



DETAIL A  
(ROTATED -90°)  
SCALE: 12X





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| AttitudeEngine™          | FRFET®   | Power Supply WebDesigner™             | TinyBoost®       |
| Awinda®                  | Global Power Resource <sup>SM</sup>            | PowerTrench®                          | TinyBuck®        |
| AX-CAP®*                 | GreenBridge™                                   | PowerXS™                              | TinyCalc™        |
| BitSiC™                  | Green FPS™                                     | Programmable Active Droop™            | TinyLogic®       |
| Build it Now™            | Green FPS™ e-Series™                           | QFET®                                 | TINYOPTO™        |
| CorePLUS™                | Gmax™  | QS™                                   | TinyPower™       |
| CorePOWER™               | GTO™   | Quiet Series™                         | TinyPWM™         |
| CROSSVOLT™               | IntelliMAX™                                    | RapidConfigure™                       | TinyWire™        |
| CTL™                     | ISOPLANAR™                                     | Saving our world, 1mW/W/kW at a time™ | TranSiC™         |
| Current Transfer Logic™  | Making Small Speakers Sound Louder and Better™ | SignalWise™                           | TriFault Detect™ |
| DEUXPEED®                | MegaBuck™                                      | SmartMax™                             | TRUECURRENT®*    |
| Dual Cool™               | MICROCOUPLER™                                  | SMART START™                          | μSerDes™         |
| EcoSPARK®                | MicroFET™                                      | Solutions for Your Success™           | UHC®             |
| EfficientMax™            | MicroPak™                                      | SPM®                                  | Ultra FRFET™     |
| ESBC™                    | MicroPak2™                                     | STEALTH™                              | UniFET™          |
| F <sup>®</sup>           | MillerDrive™                                   | SuperFET®                             | VCX™             |
| Fairchild®               | MotionMax™                                     | SuperSOT™-3                           | VisualMax™       |
| Fairchild Semiconductor® | MotionGrid®                                    | SuperSOT™-6                           | VoltagePlus™     |
| FACT Quiet Series™       | MTi®   | SuperSOT™-8                           | XST™             |
| FACT®                    | MTx®   | SupreMOS®                             | Xsens™           |
| FastvCore™               | MVN®   | SyncFET™                              | 仙童®              |
| FETBench™                | mWSaver®                                       | Sync-Lock™                            |                  |
| FPS™                     | OptoHiT™                                       |                                       |                  |
|                          | OPTOLOGIC®                                     |                                       |                  |

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**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
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